

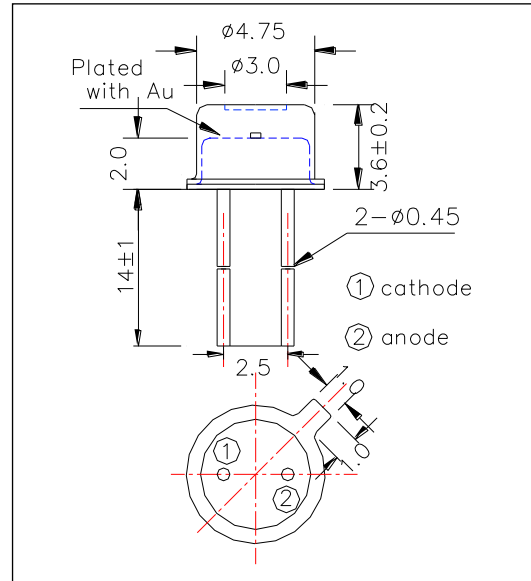
PD1450-35T54T
Stem Type Photodiode

Preliminary

<Specifications>

- Chip Material: InGaAs
- Chip Dimension: 380um x 380um
- Number of Chips: 1pcs
- Stem: TO-18 type
- Lens: Flat Glass
- Cap: Gold Plated

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Reverse Breakdown Voltage	VR	20	V
Operating Temperature	TOPR	-40 ~ + 100	°C
Storage Temperature	TSTG	-40 ~ + 100	°C
Soldering Temperature*	TSOL	250	°C

* Soldering condition must be completed within 5 seconds at 265°C and is allowed in the area apart 3mm from the bottom of the diode.

Electro-Optical Characteristics [Ta=25°C]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Photo Responsibility	RE	λP=1300nm		0.95		A/W
		λP=1550nm		1.00		
Photo Current*	IL	VR=5V, λP=1450nm		18		uA
Dark Current	ID	VR=5V			1	nA
Spectral Responsibility(Peak)	λP	VR=0V		1450		nm
Half Angle of Sensitivity	θ1/2	VR=0V		±29		deg
Total Capacitance	CT	VR=5V f=1MHz		4.5		pF

* Measured by UEI's calibrated tool



Disclaimer

Product specifications and data shown in this product catalog are subject to change without notice for the purposes of improving product performance, reliability, design, or otherwise.

Product data and parameters in this catalog are typical values based on reasonably up-to-date measurements. Product data and parameters may vary by user application and over time.

Products shown in this catalog are intended to be used for general electronic equipment. Products are not guaranteed for applications where product malfunction or failure may cause personal injury or death, including but not limited to life-supporting / saving devices, medical devices, safety devices, airplanes, aerospace equipment, automobiles, traffic control systems, and nuclear reactor control systems.

2016.06